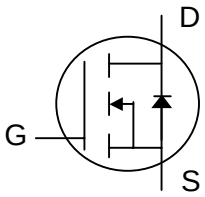
N-channel Enhancement-mode Power MOSFET

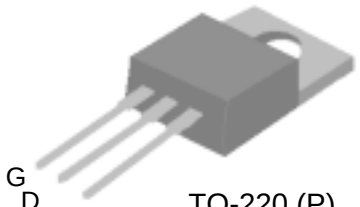
Dynamic dv/dt rating
Repetitive Avalanche Rated
Fast Switching
Simple Drive Requirement



BV_{DSS}	675V
$R_{DS(ON)}$	1.2Ω
I_D	7A

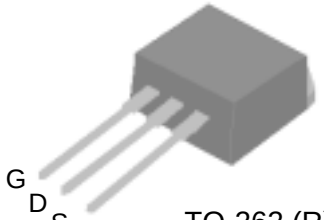
DESCRIPTION

The SSM07N70C series is specially designed as a main switching device for universal 90~265VAC off-line AC/DC converter applications.
Both TO-220 and TO-262 type provide high blocking voltage to overcome voltage surge and sag in the toughest power system with the best combination of fast switching,ruggedized design and cost-effectiveness.



TO-220 (P)

The TO-220 and TO-262 packages are widely preferred for all commercial and industrial applications. The device is well suited for switch-mode power supplies, AC-DC converters and high-current high-speed switching circuits.



TO-262 (R)

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	675	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D @ T_C=25°C	Continuous Drain Current, V_{GS} @ 10V	7	A
I_D @ T_C=100°C	Continuous Drain Current, V_{GS} @ 10V	4.4	A
I_{DM}	Pulsed Drain Current[1]	18	A
P_D @ T_C=25°C	Total Power Dissipation	89	W
	Linear Derating Factor	0.7	W/°C
E_{AS}	Single Pulse Avalanche Energy[2]	140	mJ
I_{AR}	Avalanche Current	7	A
E_{AR}	Repetitive Avalanche Energy	7	mJ
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

THERMAL DATA

Symbol	Parameter		Value	Unit
Rthj-c	Thermal Resistance Junction-case	Max.	1.4	°C/W
Rthj-a	Thermal Resistance Junction-ambient	Max.	62	°C/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=1mA	675	-	-	V
$\Delta BV_{DSS}/\Delta Tj$	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I_D=1mA	-	0.6	-	V/°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=3.5A	-	-	1.2	Ω
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	2	-	4	V
g_{fs}	Forward Transconductance	V_{DS}=10V, I_D=3.5A	-	4.5	-	S
I_{DSS}	Drain-Source Leakage Current (T_j=25°C)	V_{DS}=675V, V_{GS}=0V	-	-	10	uA
	Drain-Source Leakage Current (T_j=150°C)	V_{DS}=480V, V_{GS}=0V	-	-	100	uA
I_{GSS}	Gate-Source Leakage	V_{GS}= ± 30V	-	-	±100	nA
Q_g	Total Gate Charge[3]	I_D=7A	-	32	-	nC
Q_{gs}	Gate-Source Charge	V_{DS}=480V	-	8.6	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=10V	-	9	-	nC
$t_{d(on)}$	Turn-on Delay Time[3]	V_{DD}=300V	-	17	-	ns
t_r	Rise Time	I_D=7A	-	15	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=10Ω, V_{GS}=10V	-	35	-	ns
t_f	Fall Time	R_D=43Ω	-	18	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	2075	-	pF
C_{oss}	Output Capacitance	V_{DS}=25V	-	120	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	8	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_S	Continuous Source Current (Body Diode)	V_D=V_G=0V , V_S=1.5V	-	-	7	A
I_{SM}	Pulsed Source Current (Body Diode)[1]		-	-	18	A
V_{SD}	Forward On Voltage[3]	T_j=25°C, I_S=7A, V_{GS}=0V	-	-	1.5	V

Notes:

1.Pulse width limited by safe operating area.

2.Starting T_j=25°C , V_{DD}=50V , L=5mH , R_G=25Ω , I_{AS}=7A.

3.Pulse width ≤300us , duty cycle ≤2%.

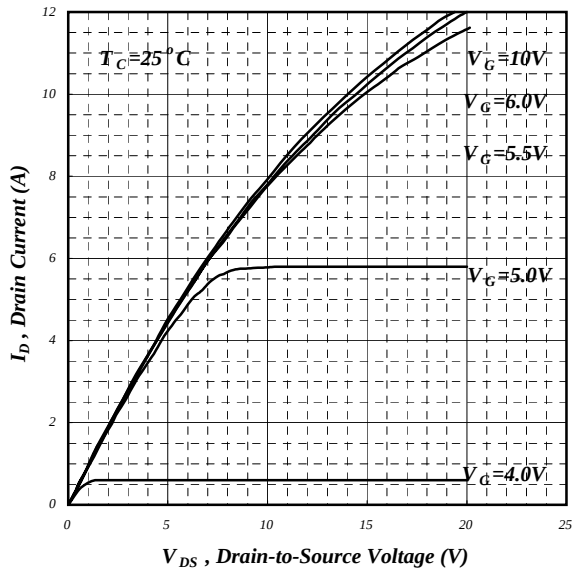


Fig 1. Typical Output Characteristics

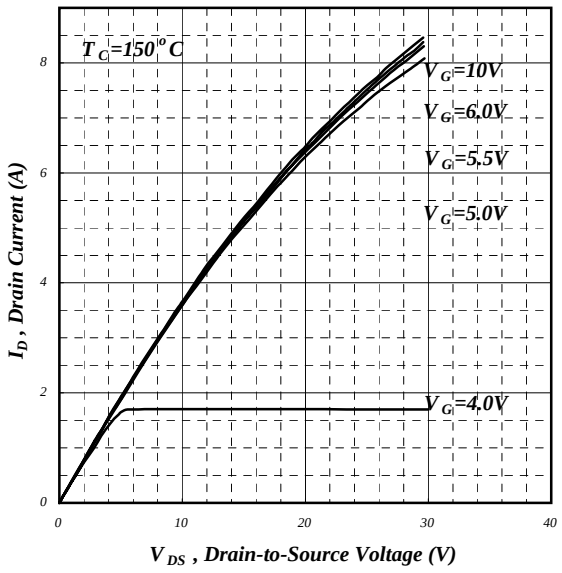


Fig 2. Typical Output Characteristics

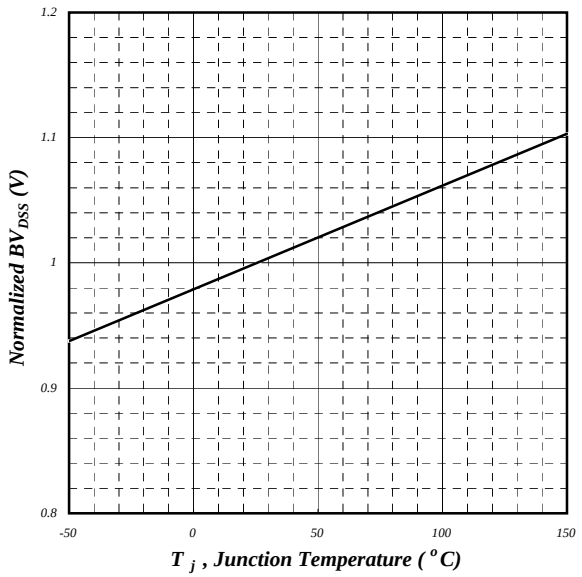


Fig 3. Normalized BV_{DSS} vs. Junction Temperature

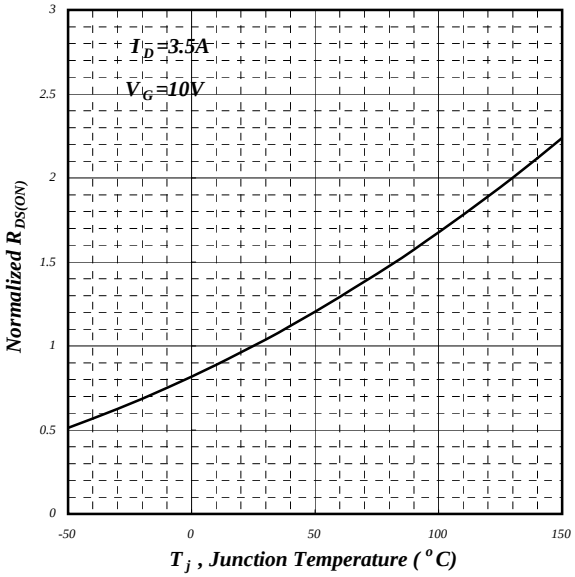


Fig 4. Normalized On-Resistance vs. Junction Temperature

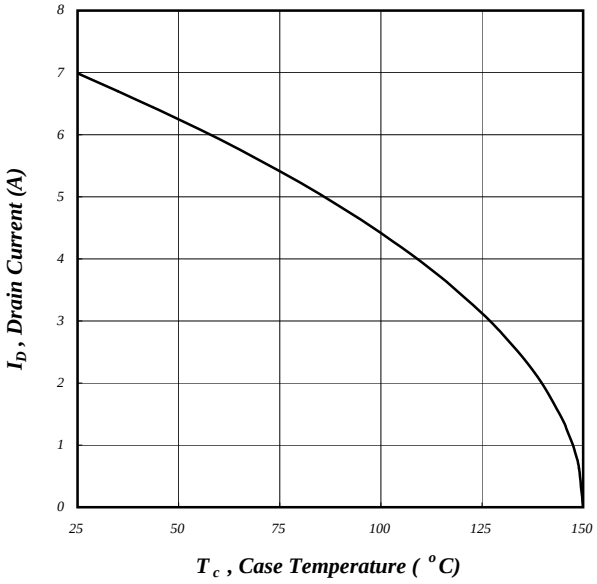


Fig 5. Maximum Drain Current vs. Case Temperature

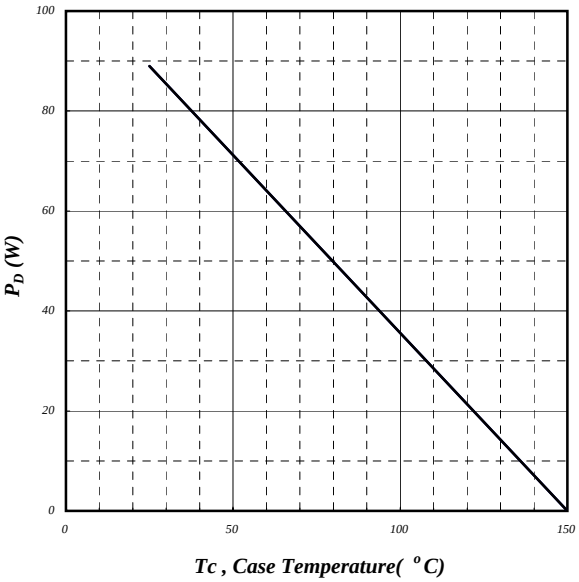


Fig 6. Typical Power Dissipation

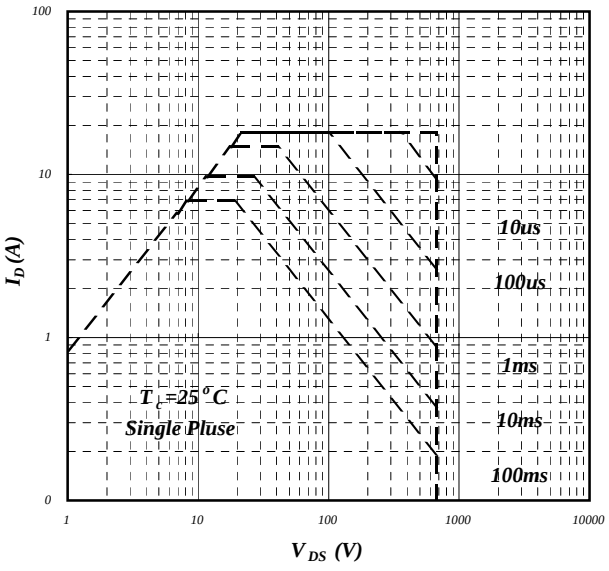


Fig 7. Maximum Safe Operating Area

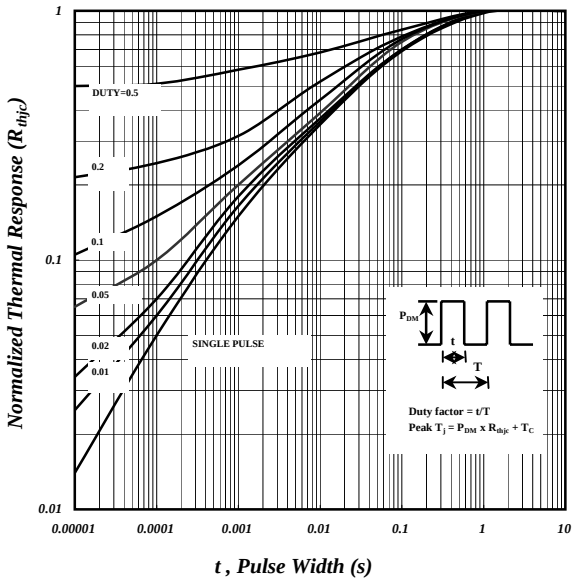


Fig 8. Effective Transient Thermal Impedance

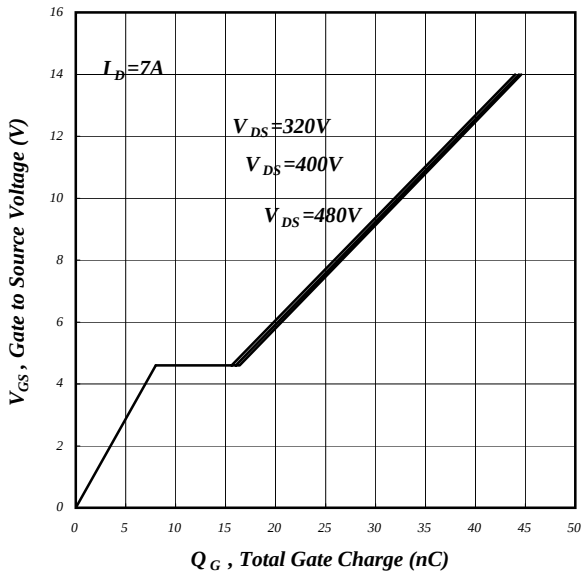


Fig 9. Gate Charge Characteristics

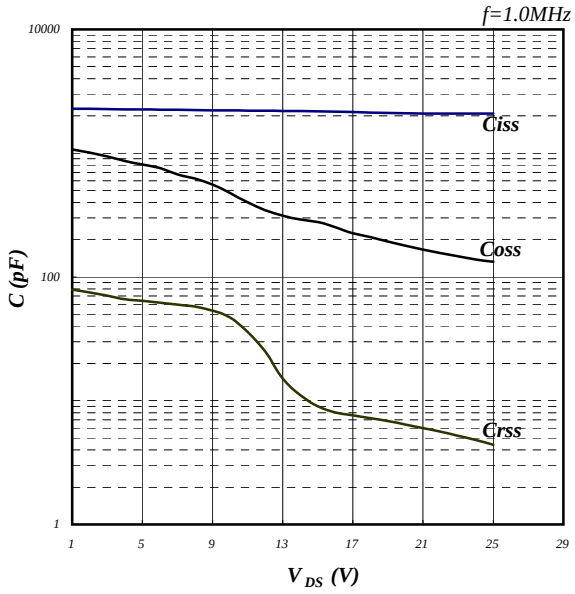


Fig 10. Typical Capacitance Characteristics

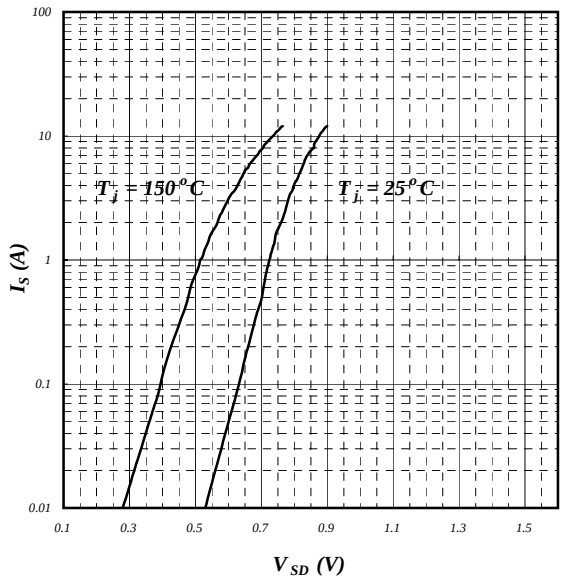


Fig 11. Forward Characteristic of Reverse Diode

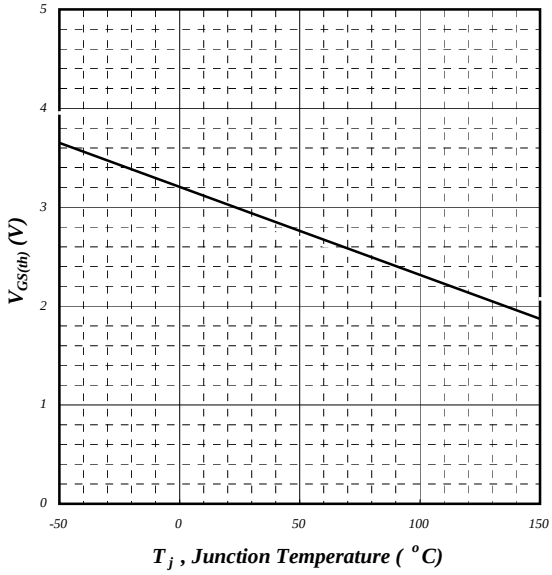


Fig 12. Gate Threshold Voltage vs. Junction Temperature

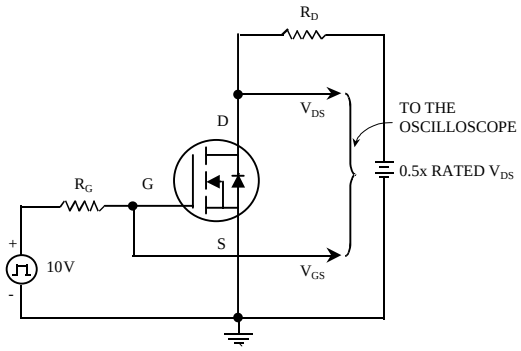


Fig 13. Switching Time Circuit

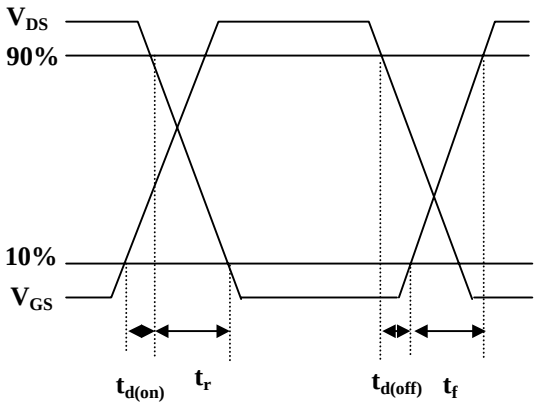


Fig 14. Switching Time Waveform

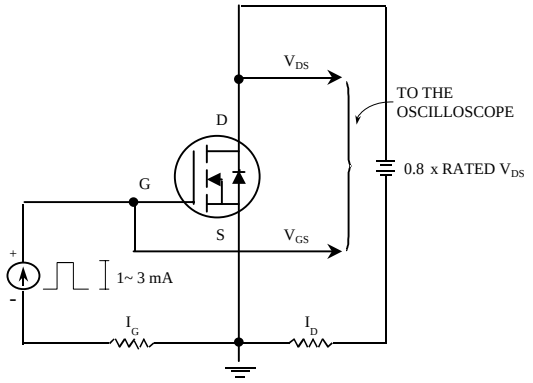


Fig 15. Gate Charge Circuit

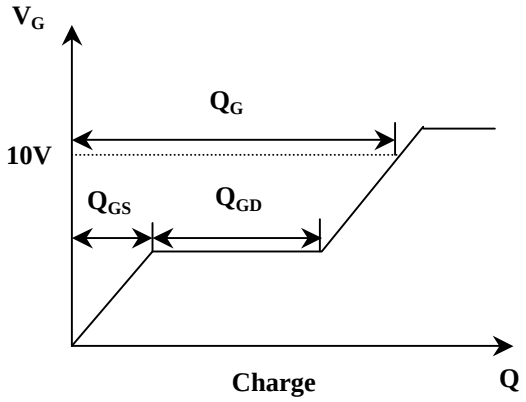


Fig 16. Gate Charge Waveform